50V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_A = +25°C
50V	2Ω @V_{GS} = 5V	480mA
	2.5Ω @V_{GS} = 2.5V	440mA
	4Ω @V_{GS} = 1.8V	370mA

Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

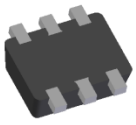
- Battery management systems
- Power management functions
- Load switches

Mechanical Data

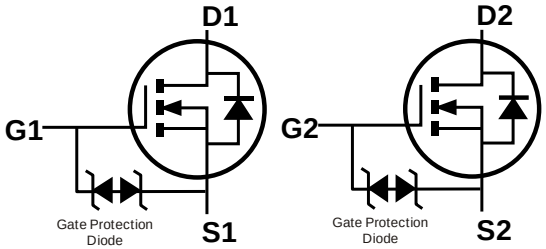
- Package: SOT563
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

SOT563

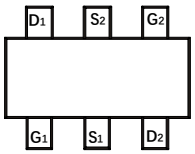
Top View



Bottom View



Equivalent Circuit



Top View

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN52D0UVA-7	SOT563	3,000	Reel
DMN52D0UVA-13	SOT563	10,000	Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

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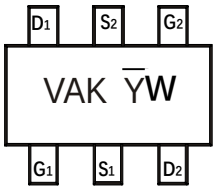
Marking Information



VAK = Product Type Marking Code
YW = Date Code Marking
Y = Year (ex: 2 = 2022)
W = Week (ex: a = week 27; z represents week 52 and 53)

Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	2	3	4	5	6	7	8	9	0	1	2	3

Week	1-26	27-52	53
Code	A-Z	a-z	z

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	50	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 6) V_{GS} = 5V	Steady State	T_A = +25°C T_A = +70°C	I_D	480 380	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	480	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	1.2	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	1.2	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.48	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	261	°C/W
Total Power Dissipation (Note 6)		P_D	0.89	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	139	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 50V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.49	—	1.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.6	4.0	Ω	V_{GS} = 1.8V, I_D = 50mA
		—	1.2	2.5		V_{GS} = 2.5V, I_D = 50mA
		—	1.0	2.0		V_{GS} = 5.0V, I_D = 50mA
Diode Forward Voltage	V_{SD}	—	0.6	1.2	V	V_{GS} = 0V, I_D = 50mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	39	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	4.8	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	3.6	—	pF	
Gate Resistance	R_g	—	47.8	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	0.8	—	nC	V_{DS} = 25V, I_D = 50mA
Total Gate Charge (V_{GS} = 10V)	Q_g	—	1.5	—	nC	
Gate-Source Charge	Q_{gs}	—	0.1	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	1.05	—	ns	V_{DS} = 25V, V_{GS} = 10V, R_G = 50Ω, I_D = 50mA
Turn-On Rise Time	t_R	—	11.3	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	33	—	ns	
Turn-Off Fall Time	t_F	—	38.5	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

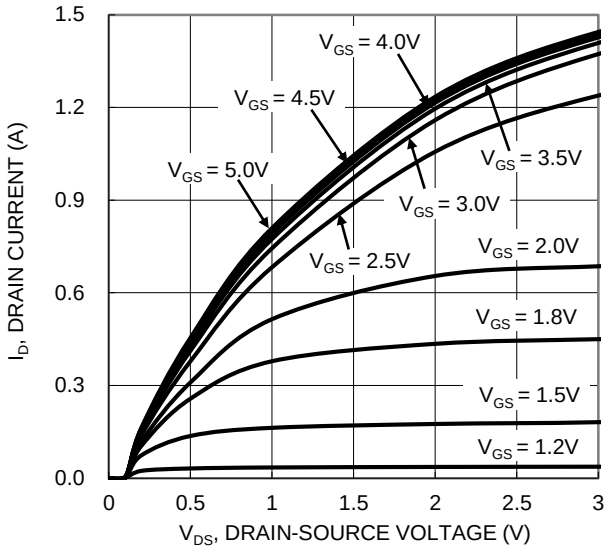


Figure 1. Typical Output Characteristic

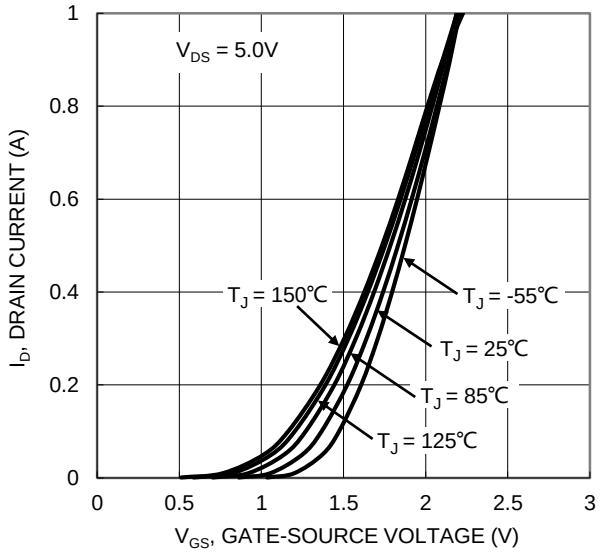


Figure 2. Typical Transfer Characteristic

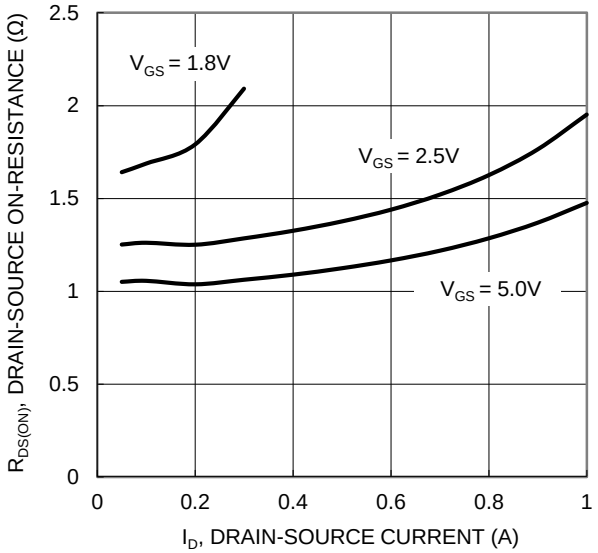


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

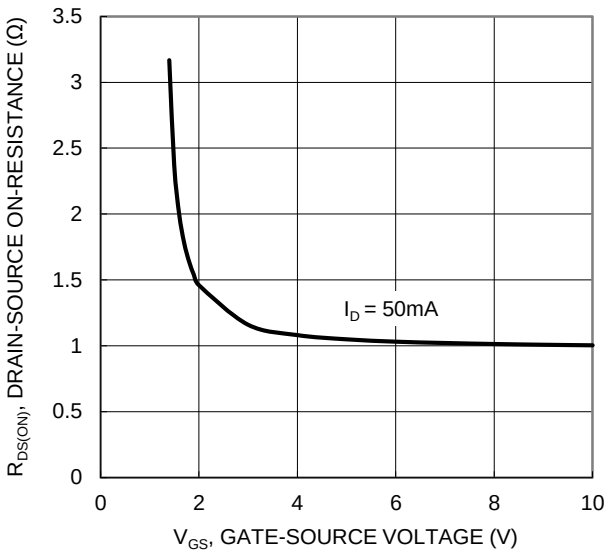


Figure 4. Typical Transfer Characteristic

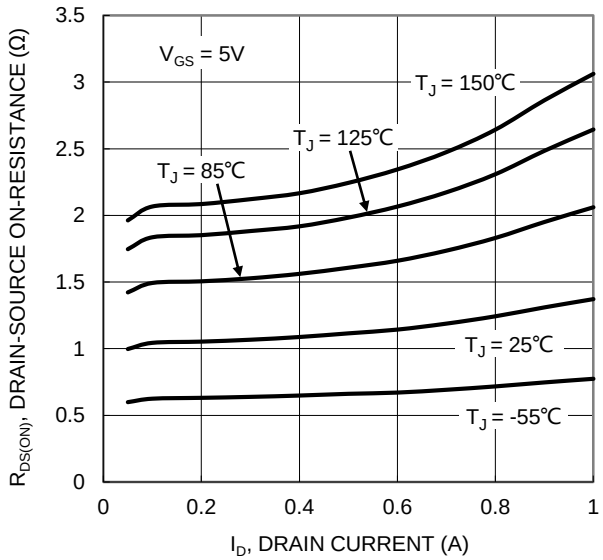


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

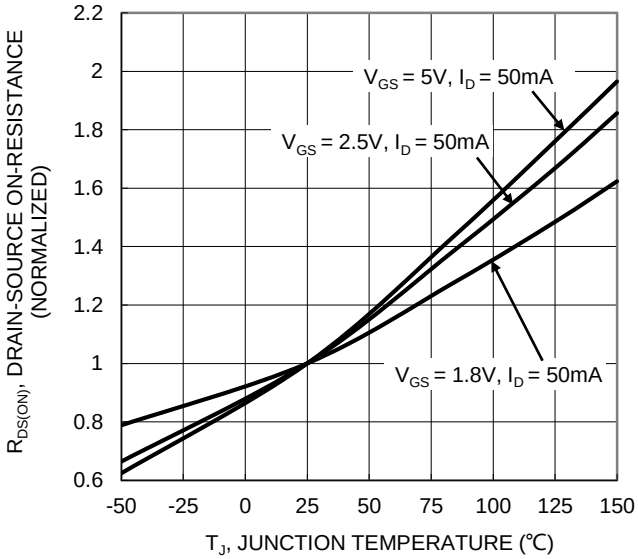


Figure 6. On-Resistance Variation with Junction Temperature

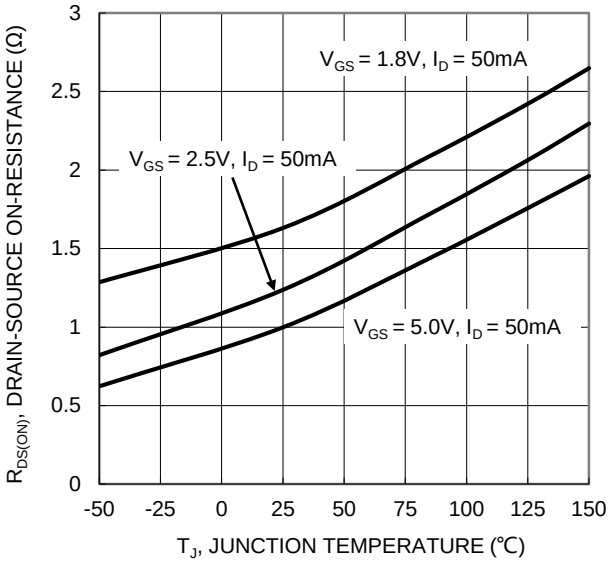


Figure 7. On-Resistance Variation with Junction Temperature

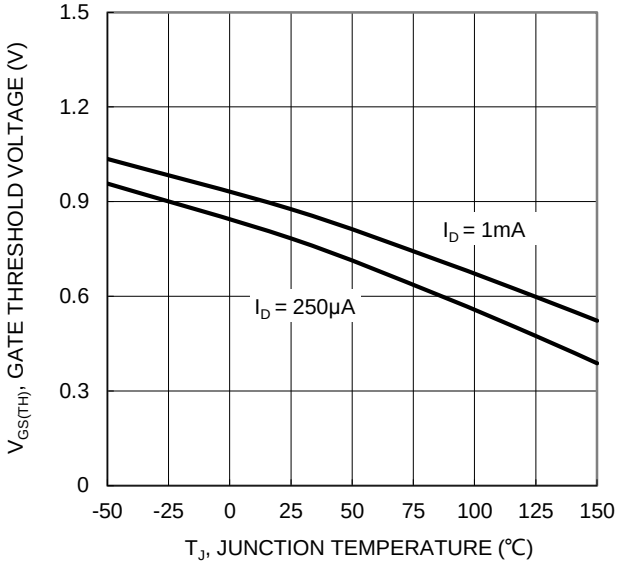


Figure 8. Gate Threshold Variation vs. Junction Temperature

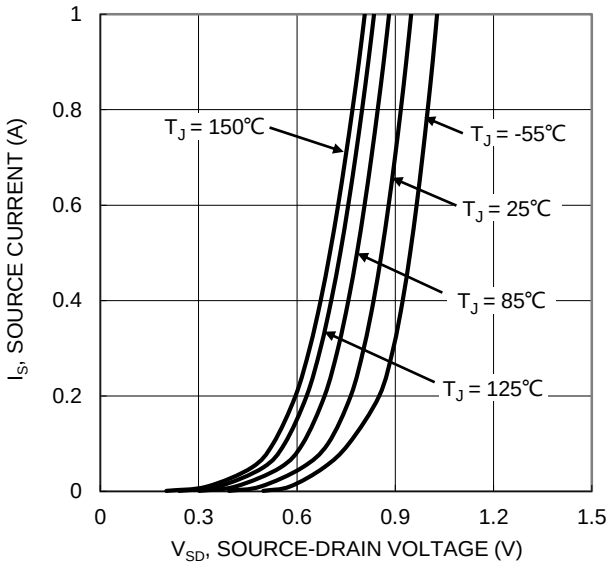


Figure 9. Diode Forward Voltage vs. Current

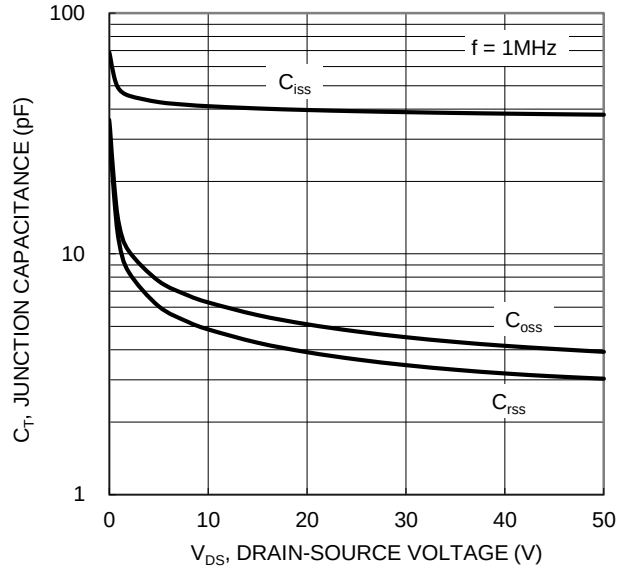


Figure 10. Typical Junction Capacitance

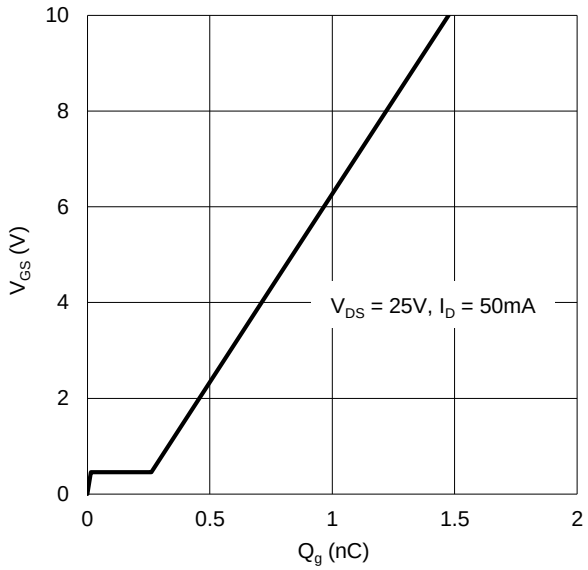


Figure 11. Gate Charge

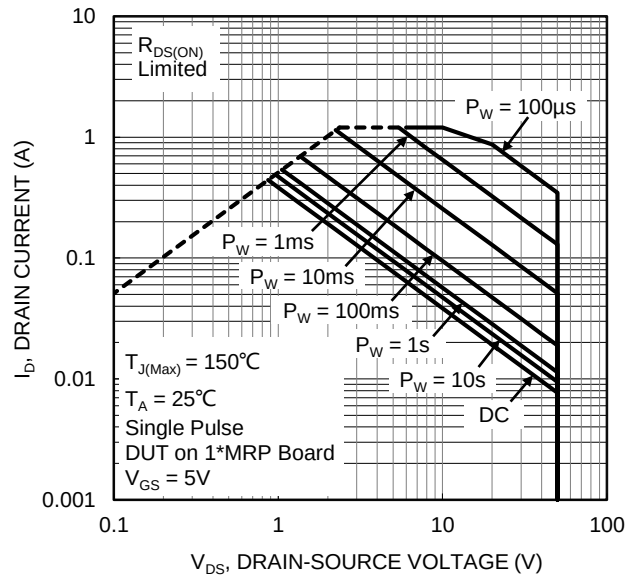


Figure 12. SOA, Safe Operation Area

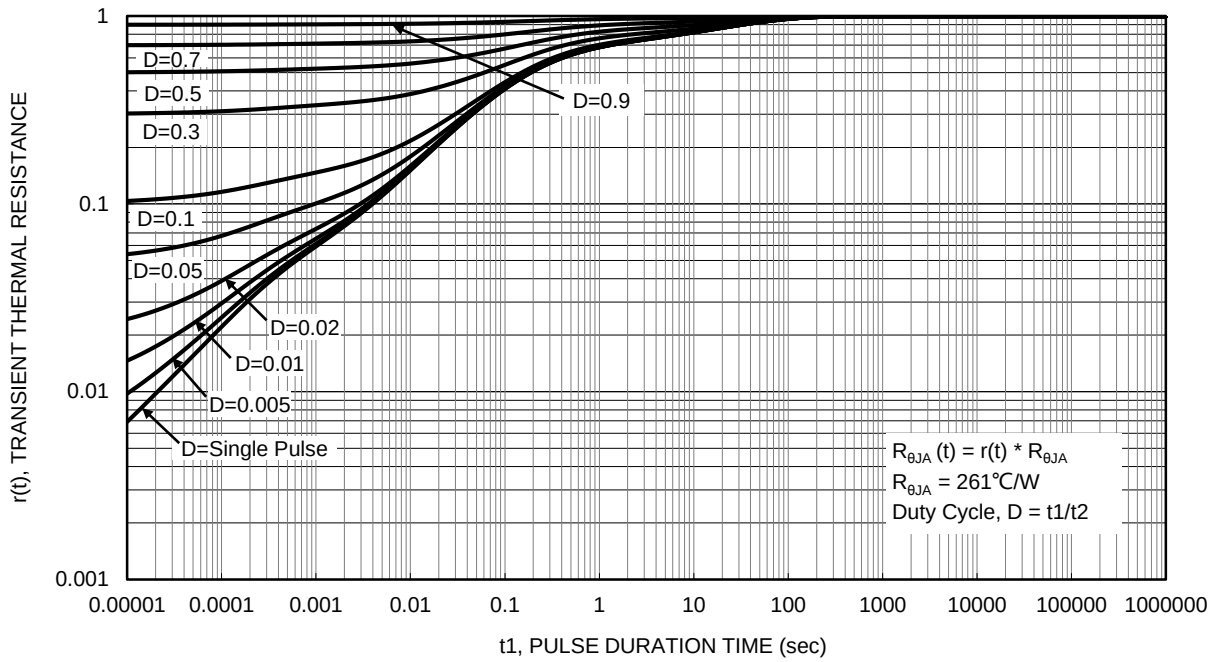
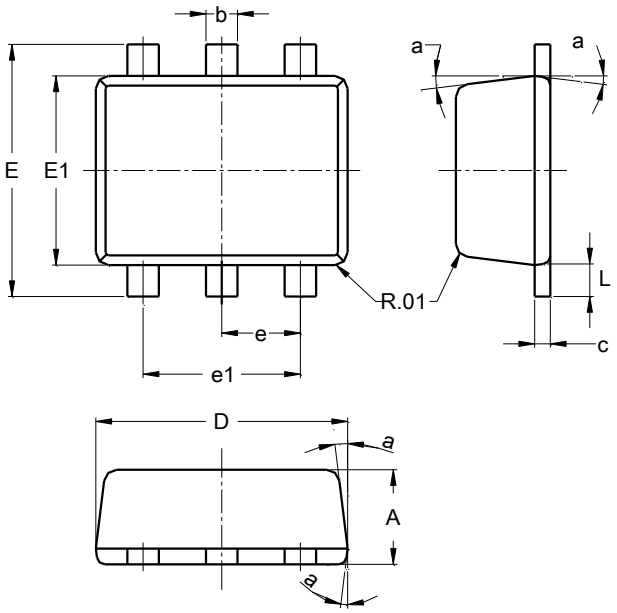


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563

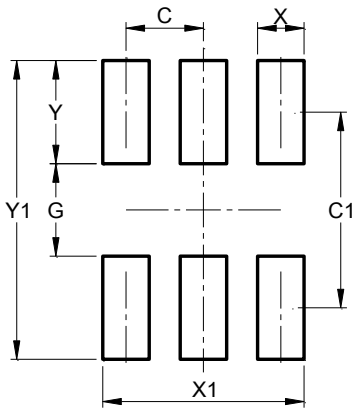


SOT563			
Dim	**Min**	**Max**	**Typ**
A	0.55	0.60	--
b	0.15	0.30	0.20
c	0.10	0.18	0.11
D	1.50	1.70	1.60
E	1.55	1.70	1.60
E1	1.10	1.25	1.20
e	--	--	0.50
e1	0.90	1.10	1.00
L	0.10	0.30	0.20
a	8°	9°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563



Dimensions	Value (in mm)
C	0.500
C1	1.270
G	0.600
X	0.300
X1	1.300
Y	0.670
Y1	1.940

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